



APPLICATION

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Applications such as Cell Phones, Digital Cameras ,PDAs, etc

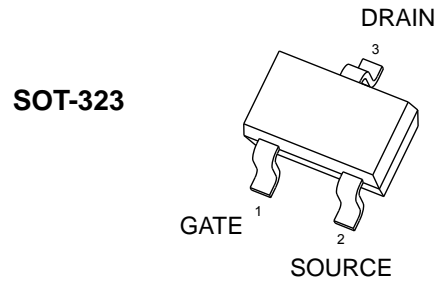
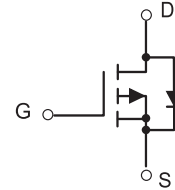
FEATURE

- Leading Trench Technology for Low $R_{DS(on)}$ Extending Battery Life

P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	155mΩ@-4.5V	-1.4A
	240mΩ@-2.5V	
	390mΩ@-1.8V	

PACKAGE



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	±8.0	
Continuous Drain Current	I_D	-1.4	A
Pulsed Drain Current ($t_p=10\mu s$)	I_{DM}	-3.0	
Power Dissipation	P_D	0.29	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	431	$^{\circ}C/W$
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55 ~+150	$^{\circ}C$



MOSFET ELECTRICAL CHARACTERISTICS

Ta=25 °C unless otherwise specified

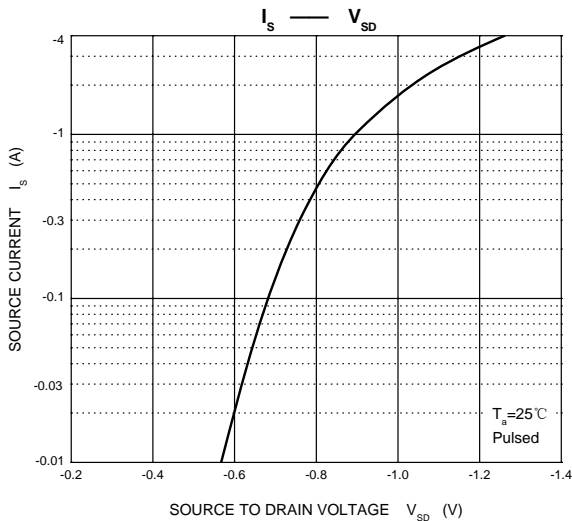
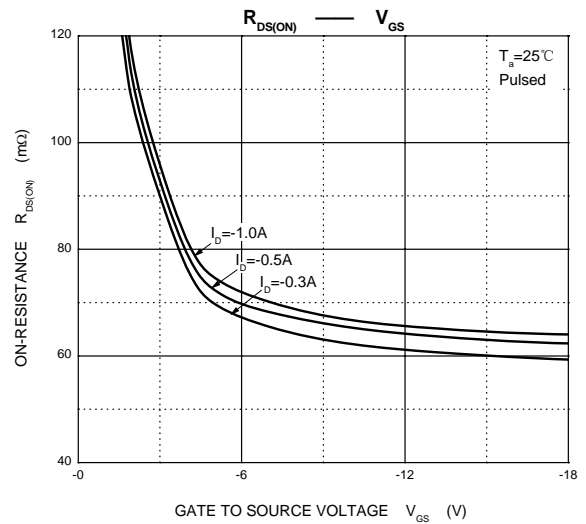
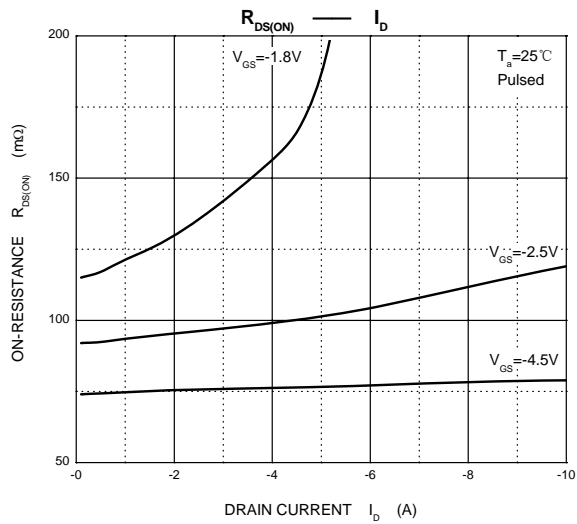
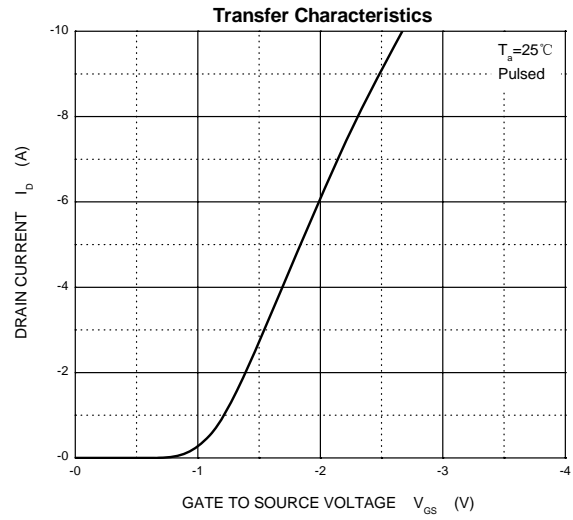
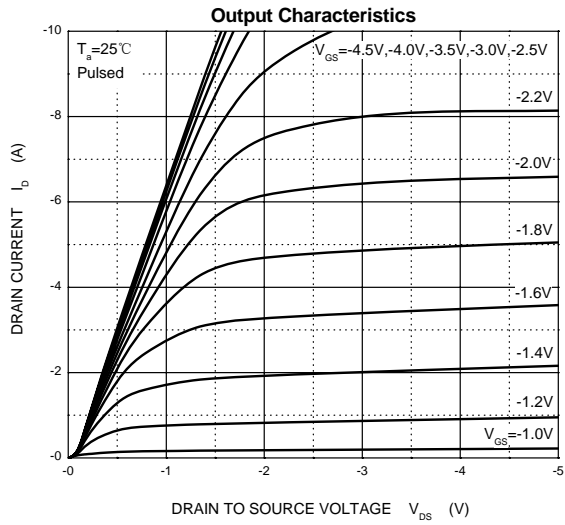
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISSTICS						
Drain-Source Breakdown Voltage	V _{DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V			-1.0	μA
OFF CHARACTERISSTICS (note 1)						
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.45	-0.7		V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -1.0A		120	155	mΩ
		V _{GS} = -2.5V, I _D = -0.5A		202	240	
		V _{GS} = -1.8V, I _D = -0.3A		320	390	
CHARGES AND CAPACITANCES (note 3)						
Input Capacitance	C _{iss}	V _{DS} = -8.0V, V _{GS} = 0V, f = 1MHz		640		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			82		
SWITCHING CHARACTERISSTICS (note 2,3)						
Turn-On Delay Time	t _{d(on)}	V _{GS} = -4.5V, V _{DD} = -4.0V, I _D = -1.0A, R _G = 6.2Ω		6.2		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(off)}			26		
Fall Time	t _f			18		
Total Gate Charge	Q _g	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -3.0A		5.5	10	nC
Gate-Source Charge	Q _{gs}	V _{DS} = -10V, V _{GS} = -2.5V, I _D = -3.0A		3.3	6	
Gate-Drain Charge	Q _{gd}			0.7		
				1.3		
Drain-source Body diode characteristics						
Forward Diode Voltage	V _{SD}	V _{GS} = 0V, I _S = -0.3A		-0.62	-1.2	V

Notes:

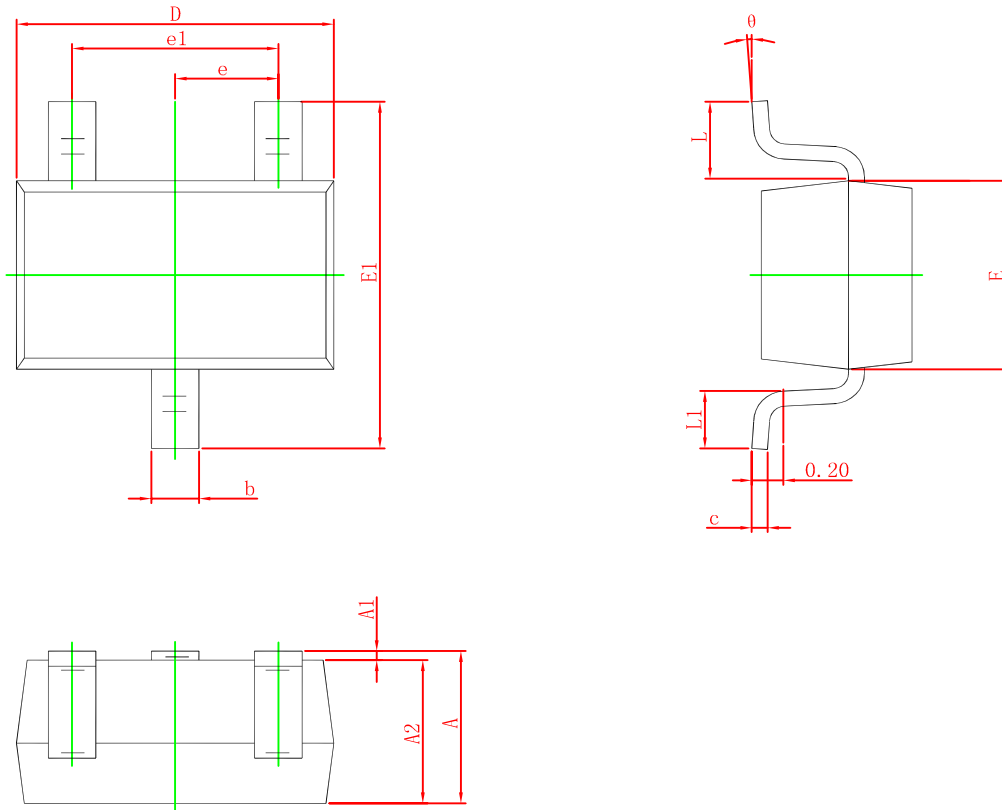
1. Pulse Test : pulse width ≤300μs, duty cycle ≤2%.
2. Switching characteristics are independent of operating junction temperatures.
3. These parameters have no way to verify.



Typical Characteristics



SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°